

## Supplementary Information

### **Enhanced Initial Coulombic Efficiency of Lithium-Ion Battery Silicon-Carbon Anodes with Phosphorus Doping**

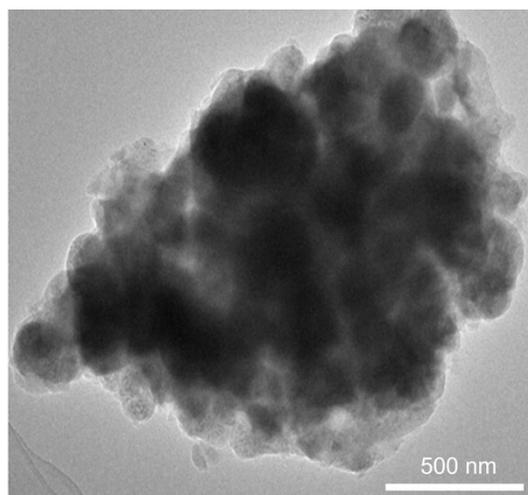
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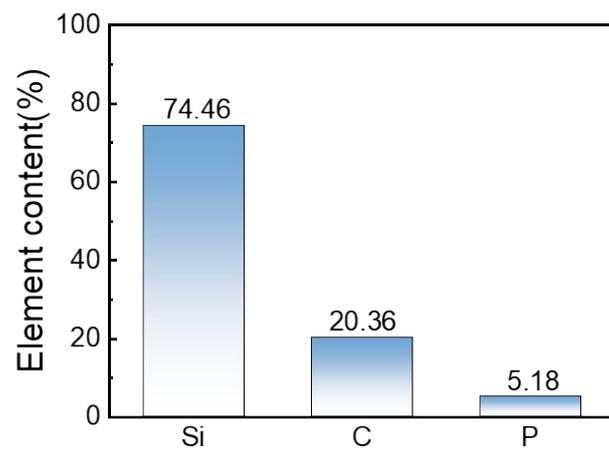
*<sup>2</sup>College of Energy Storage Technology, Shandong University of Science and Technology, Qingdao 266590, China.*

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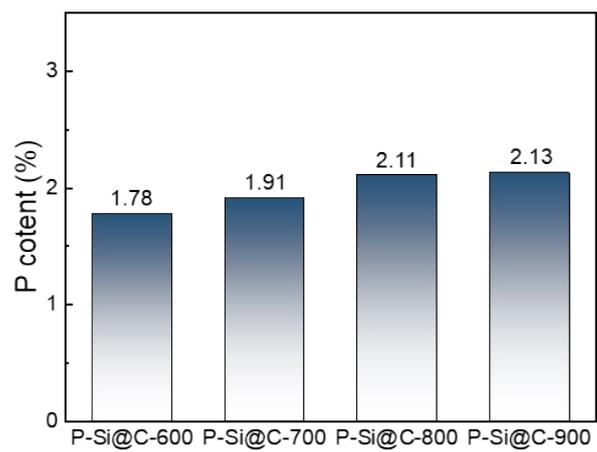
E-mail: [chenyuan@sdust.edu.cn](mailto:chenyuan@sdust.edu.cn).



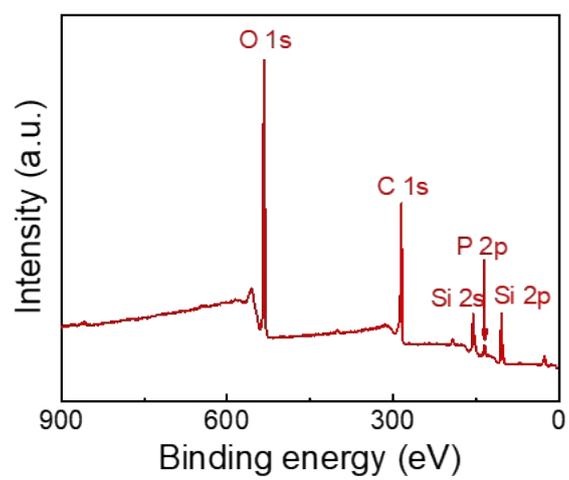
**Figure S1.** TEM images for P-Si@C.



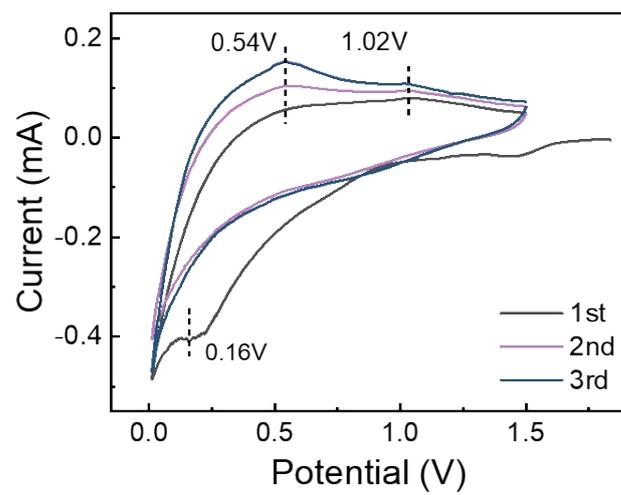
**Figure S2.** Element content of P-Si@C.



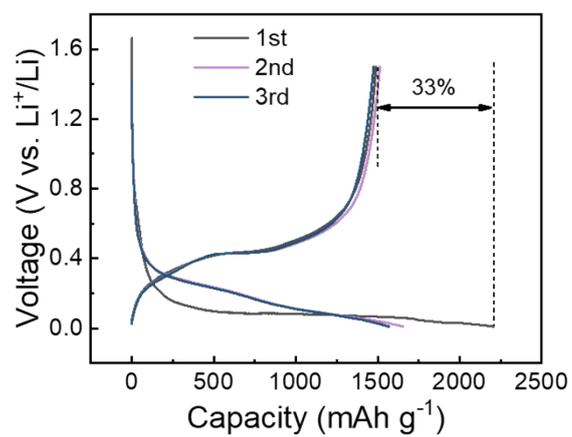
**Figure S3.** ICP results of P content.



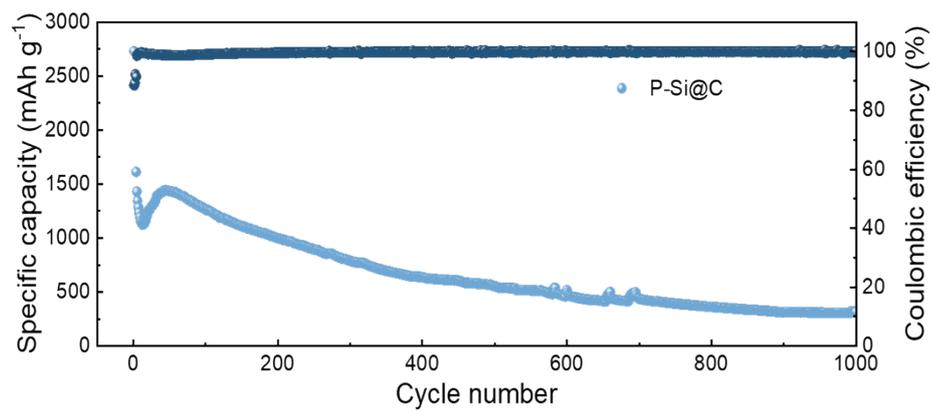
**Figure S4.** XPS survey of P-Si@C.



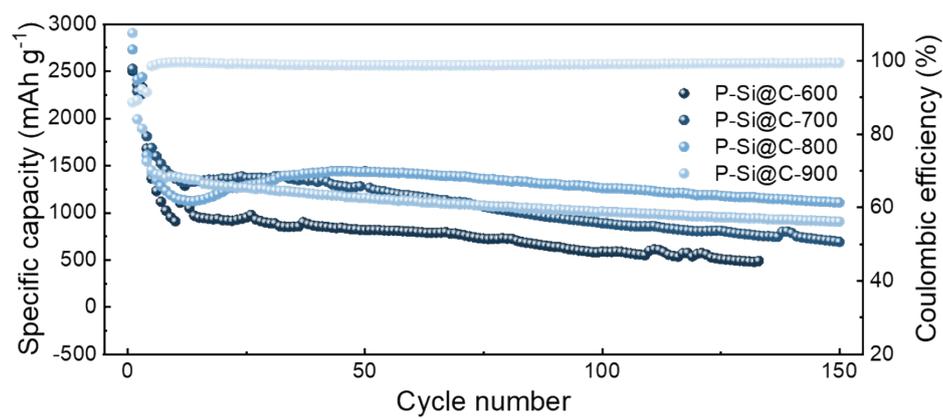
**Figure S5.** CV profiles of Si@C at 0.1 mV s<sup>-1</sup>.



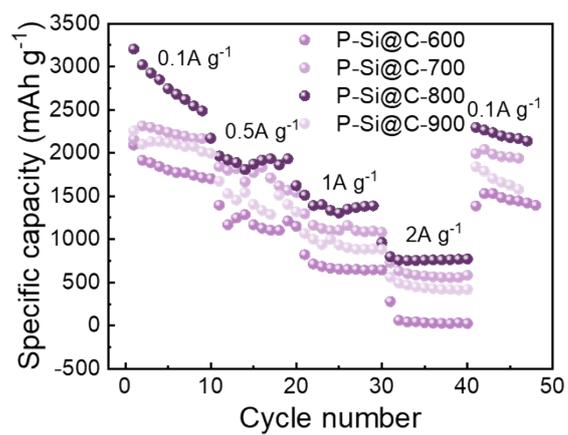
**Figure S6.** Discharge-charge voltage curves of Si@C at 100mA g<sup>-1</sup>.



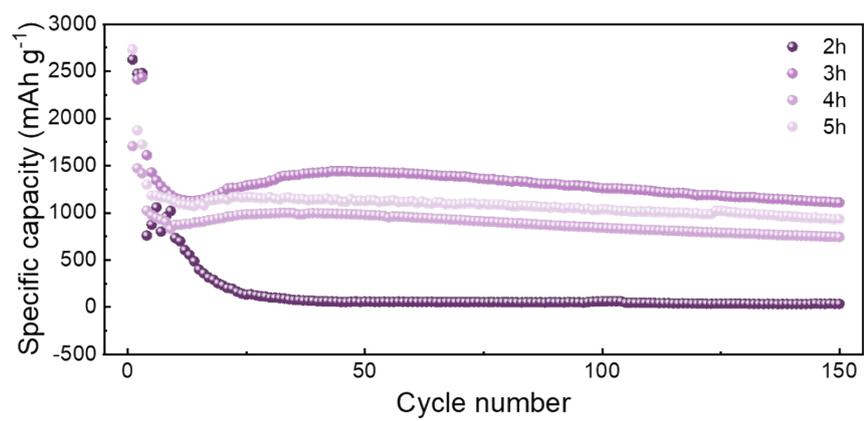
**Figure S7.** Long-term cycle performance of P-Si@C with the current density of 1.0 A g<sup>-1</sup>.



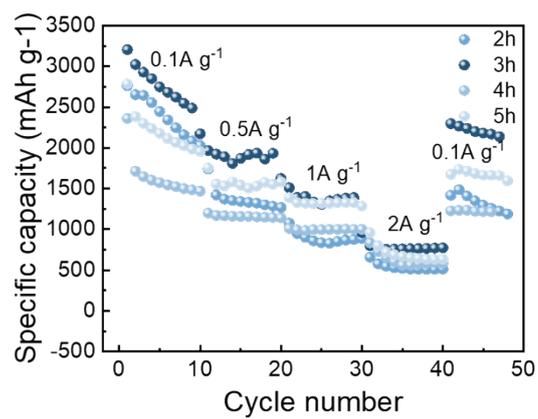
**Figure S8.** Cycling performance at  $1.0 \text{ A g}^{-1}$  of P-Si@C-600, P-Si@C-700, P-Si@C-800 and P-Si@C-900.



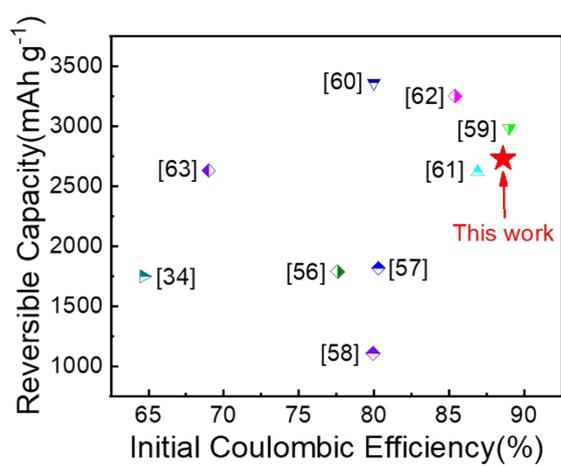
**Figure S9.** Rate performance at 1.0 A g<sup>-1</sup> of P-Si@C-600, P-Si@C-700, P-Si@C-800 and P-Si@C-900.



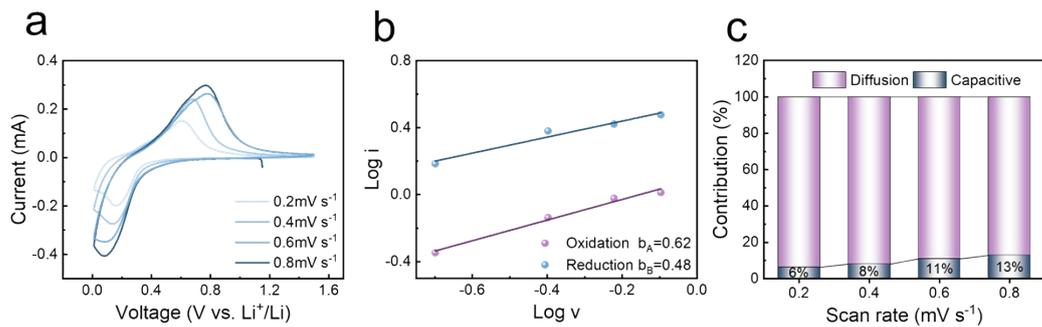
**Figure S10.** Cycling performance at 1.0 A g<sup>-1</sup> of 2h, 3h, 4h and 5h.



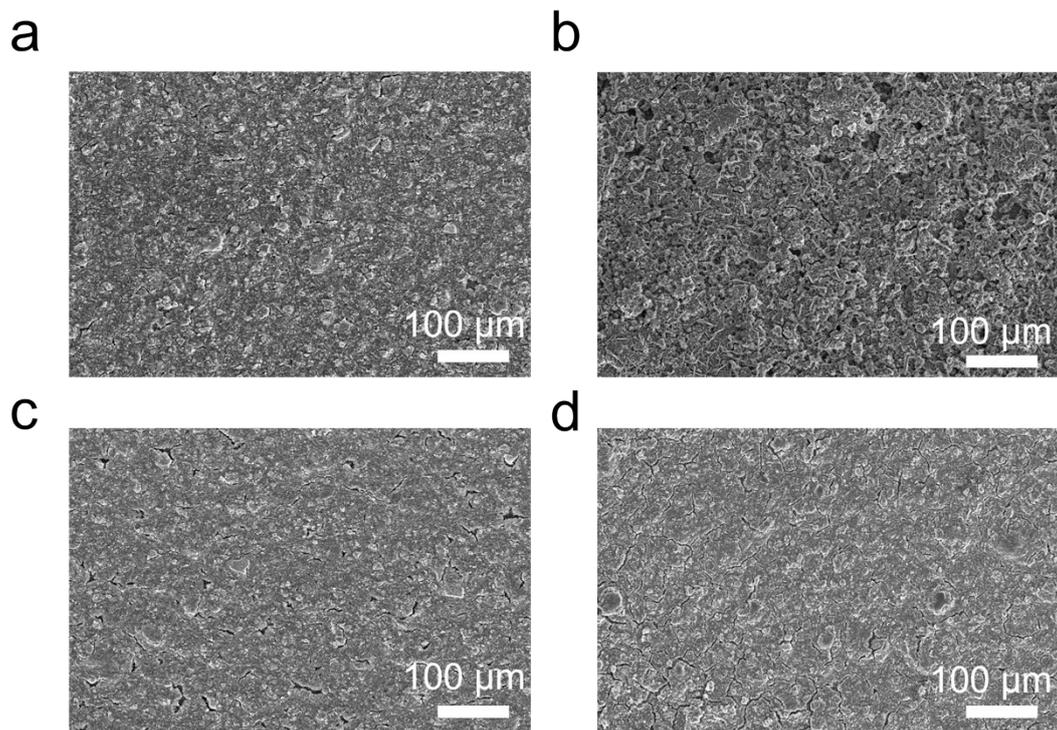
**Figure S11.** Rate performance at 1.0 A g<sup>-1</sup> of 2h, 3h, 4h and 5h.



**Figure S12.** Comparison of the ICE and reversible capacity of silicon anodes with doping methods reported in the literature.



**Figure S13.** (a) CV curves of the electrode at different scan rates of Si@C. (b) Log i vs Log v Plots for electrode kinetics analysis of Si@C. (c) Capacitive and diffusion contributions to electrode charge storage at varied scan rates of Si@C.



**Figure S14.** (a) Surface topography of Si@C before cycling. (b) Surface topography of P-Si@C after 100 cycles. (c) Surface topography of Si@C before cycling. (d) Surface topography of P-Si@C after 100 cycles.